1. General description

Dual N-channel enhancement mode Field-Effect Transistor (FET) in a very small SOT363 (SC-88) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

2. Features and benefits

- Logic-level compatible
- Very fast switching
- Trench MOSFET technology
- · ESD protection up to 2 kV
- AEC-Q101 qualified

3. Applications

- Relay driver
- · High-speed line driver
- · Low-side load switch
- · Switching circuits

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit		
Per transistor	Per transistor								
V _{DS}	drain-source voltage	T _{amb} = 25 °C		-	-	60	V		
V_{GS}	gate-source voltage			-20	-	20	V		
I_D	drain current	V _{GS} = 10 V; T _{amb} = 25 °C	[1]	-	-	300	mA		
Static characte	Static characteristics (per transistor)								
R _{DSon}	drain-source on-state resistance	V_{GS} = 5 V; I_D = 50 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.01; T_j = 25 °C		-	1.3	2	Ω		

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 1 cm².



60 V, 300 mA dual N-channel Trench MOSFET

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S1	source1		
2	G1	gate1		1 + 6
3	D2	drain2	□6 □5 □4	
4	S2	source2		2 5
5	G2	gate2		- - · ·
6	D1	drain1	TSSOP6 (SOT363)	3 1 1 4
				017aaa055

6. Ordering information

Table 3. Ordering information

Type number Package					
	Name	Description	Version		
2N7002BKS		plastic, surface-mounted package; 6 leads; 0.65 mm pitch; 2.1 mm x 1.25 mm x 0.95 mm body	SOT363		

7. Marking

Table 4. Marking codes

Type number	Marking code[1]
2N7002BKS	ZT%

[1] % = placeholder for manufacturing site code

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8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
Per transist	tor			<u> </u>		
V _{DS}	drain-source voltage	T _{amb} = 25 °C		-	60	V
V_{GS}	gate-source voltage			-20	20	V
I _D	drain current	V _{GS} = 10 V; T _{amb} = 25 °C	[1]	-	300	mA
		V _{GS} = 10 V; T _{amb} = 100 °C	[1]	-	215	mA
I _{DM}	peak drain current	T_{amb} = 25 °C; single pulse; $t_p \le 10 \mu s$		-	1.2	А
P _{tot}	total power dissipation	T _{amb} = 25 °C	[2]	-	295	mW
			[1]	-	340	mW
		T _{sp} = 25 °C		-	1040	mW
Per device	'			•		-
P _{tot}	total power dissipation	T _{amb} = 25 °C	[2]	-	445	mW
Tj	junction temperature			-	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C
Source-dra	in diode			1		1
Is	source current	T _{amb} = 25 °C	[1]	-	300	mA
ESD maxim	num rating			'	'	'
V _{ESD}	electrostatic discharge voltage	НВМ	[3]	-	2	kV

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 1 cm².
- [2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.
- [3] Measured between all pins.

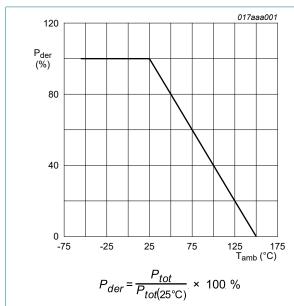


Fig. 1. Normalized total power dissipation as a function of ambient temperature

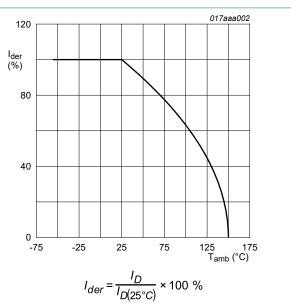
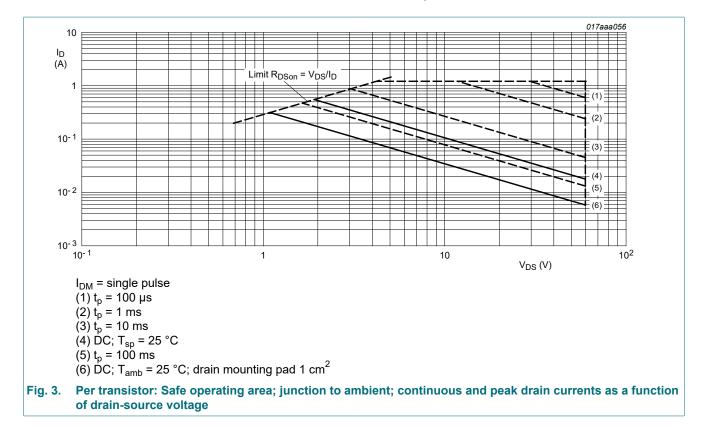


Fig. 2. Normalized continuous drain current as a function of ambient temperature

60 V, 300 mA dual N-channel Trench MOSFET



60 V, 300 mA dual N-channel Trench MOSFET

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per device			,				
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	-	275	K/W
Per transist	or		,				
R _{th(j-a)}	thermal resistance from	in free air	[1]	-	370	425	K/W
	junction to ambient		[2]	-	320	370	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point			-	-	120	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm².

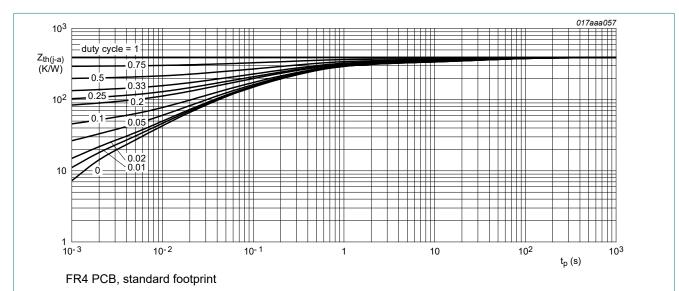
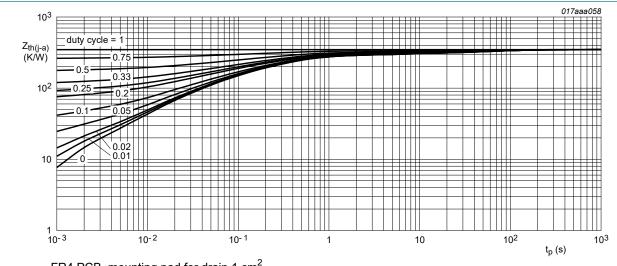


Fig. 4. Per transistor: Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



FR4 PCB, mounting pad for drain 1 cm²

Fig. 5. Per transistor: Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

2N7002BKS

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10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics (per transistor)					
V _{(BR)DSS}	drain-source breakdown voltage	$I_D = 10 \mu A; V_{GS} = 0 V; T_j = 25 °C$	60	-	-	V
V_{GSth}	gate-source threshold voltage	$I_D = 250 \mu A; V_{DS} = V_{GS}; T_j = 25 \text{ °C}$	1.1	1.6	2.1	V
I _{DSS}	drain leakage current	V _{DS} = 60 V; V _{GS} = 0 V; T _j = 25 °C	-	-	1	μΑ
		V _{DS} = 60 V; V _{GS} = 0 V; T _j = 150 °C	-	-	10	μΑ
I _{GSS}	gate leakage current	V _{GS} = 20 V; V _{DS} = 0 V; T _j = 25 °C	-	-	10	μΑ
		V _{GS} = -20 V; V _{DS} = 0 V; T _j = 25 °C	-	-	10	μΑ
R _{DSon}	drain-source on-state resistance	V_{GS} = 5 V; I_{D} = 50 mA; pulsed; t_{p} ≤ 300 μs; δ ≤ 0.01; T_{j} = 25 °C	-	1.3	2	Ω
		V_{GS} = 10 V; I_D = 500 mA; pulsed; $t_p \le$ 300 μs; $\delta \le$ 0.01; T_j = 25 °C	-	1	1.6	Ω
9 _{fs}	forward transconductance	V_{DS} = 10 V; I_{D} = 200 mA; pulsed; $t_{p} \le$ 300 μs; $\delta \le$ 0.01; T_{j} = 25 °C	-	550	-	mS
Dynamic ch	aracteristics (per transist	or)				
Q _{G(tot)}	total gate charge	V _{DS} = 30 V; I _D = 300 mA; V _{GS} = 4.5 V;	-	0.5	0.6	nC
Q _{GS}	gate-source charge	T _j = 25 °C	-	0.2	-	nC
Q _{GD}	gate-drain charge		-	0.1	-	nC
C _{iss}	input capacitance	V _{DS} = 10 V; f = 1 MHz; V _{GS} = 0 V;	-	33	50	рF
C _{oss}	output capacitance	T _j = 25 °C	-	7	-	pF
C _{rss}	reverse transfer capacitance		-	4	-	pF
t _{d(on)}	turn-on delay time	$V_{DS} = 50 \text{ V}; R_L = 250 \Omega; V_{GS} = 10 \text{ V};$	-	5	10	ns
t _r	rise time	$R_{G(ext)} = 6 \Omega; T_j = 25 °C$	-	6	-	ns
t _{d(off)}	turn-off delay time		-	12	24	ns
t _f	fall time		-	7	-	ns
Source-drai	in diode (per transistor)					
V_{SD}	source-drain voltage	I _S = 115 mA; V _{GS} = 0 V; T _i = 25 °C	0.47	0.75	1.1	V

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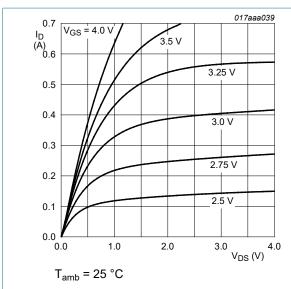
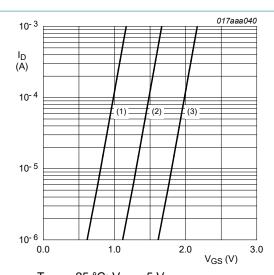


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values

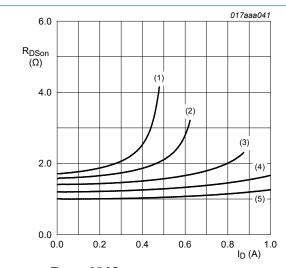


 T_{amb} = 25 °C; V_{DS} = 5 V (1) minimum values

(2) typical values

(3) maximum values

Fig. 7. Sub-threshold drain current as a function of gate-source voltage



 T_{amb} = 25 °C

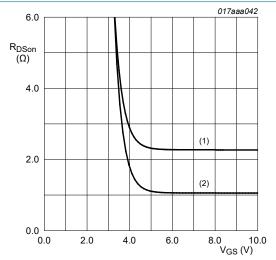
(1) $V_{GS} = 3.25 \text{ V}$

 $(2) V_{GS} = 3.5 V$

(3) $V_{GS} = 4 V$ (4) $V_{GS} = 5 V$

 $(5) V_{GS} = 10 V$

Fig. 8. Drain-source on-state resistance as a function of drain current; typical values



 $I_D = 500 \text{ mA}$

(1) T_{amb} = 150 °C

 $(2) T_{amb} = 25 °C$

Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

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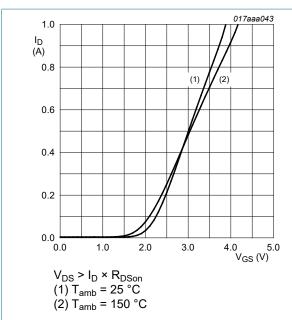


Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

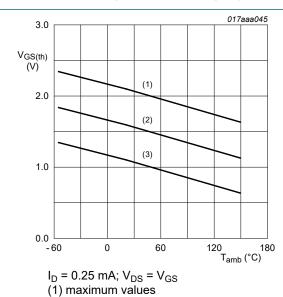


Fig. 12. Gate-source threshold voltage as a function of ambient temperature

(2) typical values

(3) minimum values

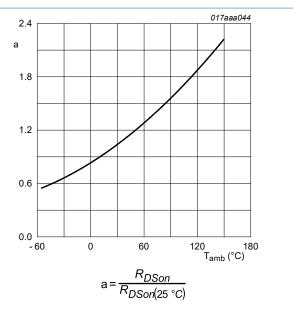
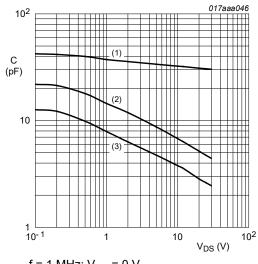


Fig. 11. Normalized drain-source on-state resistance as a function of ambient temperature; typical values



 $f = 1 MHz; V_{GS} = 0 V$

- (1) C_{iss}
- (2) C_{oss}
- (3) C_{rss}

Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

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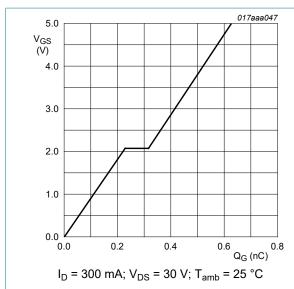


Fig. 14. Gate-source voltage as a function of gate charge; typical values

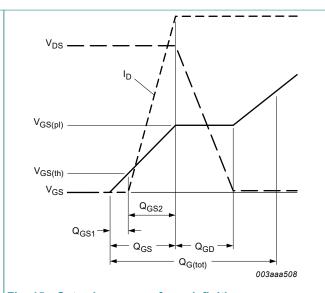
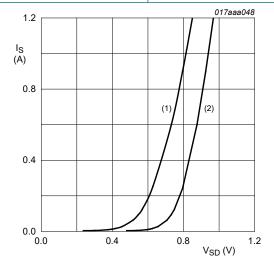


Fig. 15. Gate charge waveform definitions

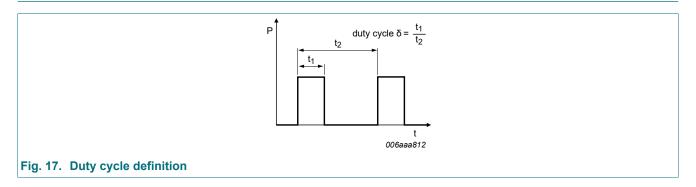


 $V_{GS} = 0 V$ (1) $T_{amb} = 150 °C$ (2) $T_{amb} = 25 °C$

Fig. 16. Source current as a function of source-drain voltage; typical values

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11. Test information



Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

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12. Package outline

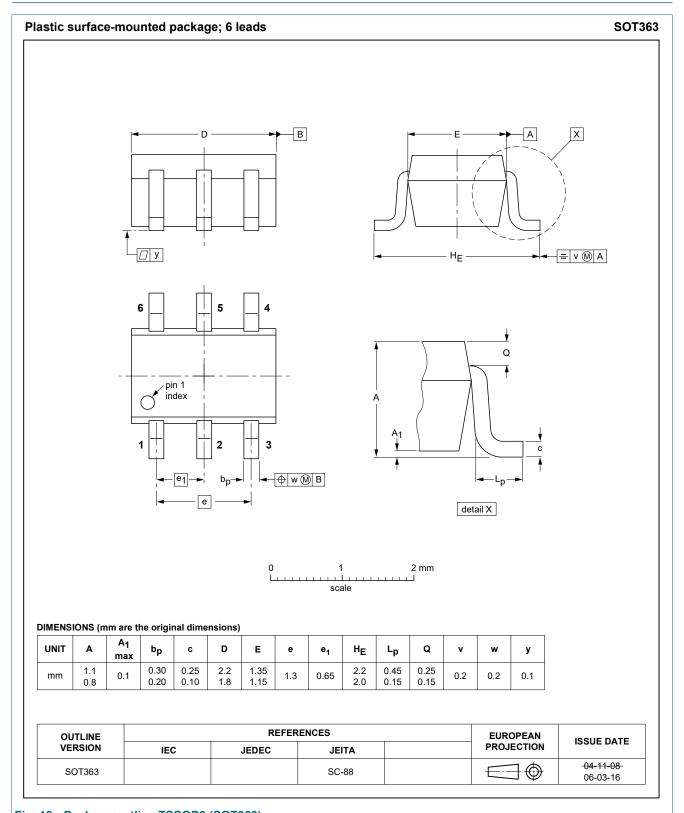
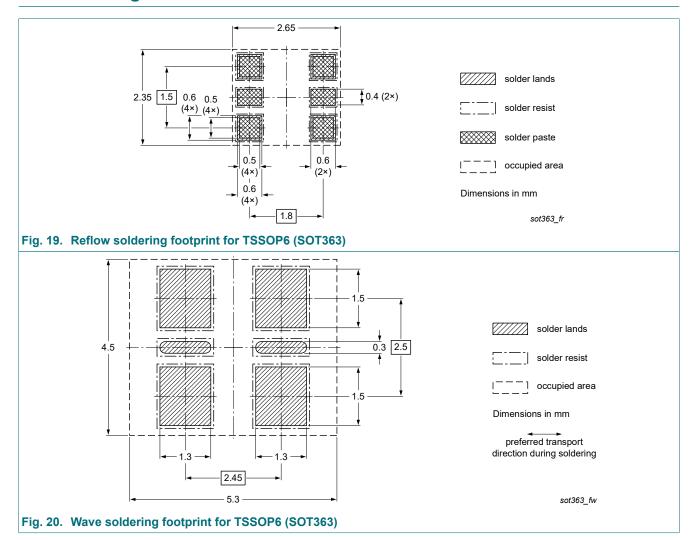


Fig. 18. Package outline TSSOP6 (SOT363)

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13. Soldering



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14. Revision history

Table 8. Revision history

iable of Revision metery								
Data sheet ID	Release date	Data sheet status	Change notice	Supersedes				
2N7002BKS v.3	20241017	Product data sheet	-	2N7002BKS v.2				
Modifications:	=	 Chapter "Characteristics": Conditions corrected for parameters t_{d(on)}, t_r, t_{d(off)}, t_f Chapter "Characteristics": Conditions corrected for Fig. 14 						
2N7002BKS v.2	20100923	Product data sheet	-	2N7002BKS v.1				
2N7002BKS v.1	20100617	Product data sheet	-	-				

Product data sheet

15. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
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